

To: BGT /

Panasonic

No. 3708131-01

Date: Oct. 13. 2006

中高圧用円板形セラミックコンデンサ KGEシリーズ
High Voltage Ceramic Disc Capacitor KGE Series

技術データ
Technical Data

パナソニック エレクトロニックデバイス株式会社
回路部品ビジネスユニット
Circuit Components Business Unit
Panasonic Electronic Devices Co., LTD.

パナソニックCC宮崎株式会社
セラミックコンデンサビジネスチーム
Panasonic Communications Miyazaki Co.,Ltd
Ceramic Capacitors Business Team

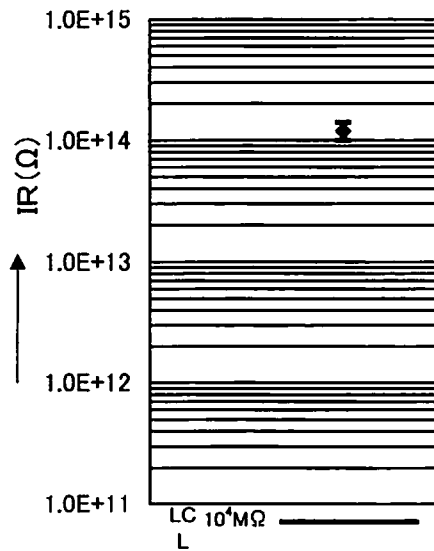
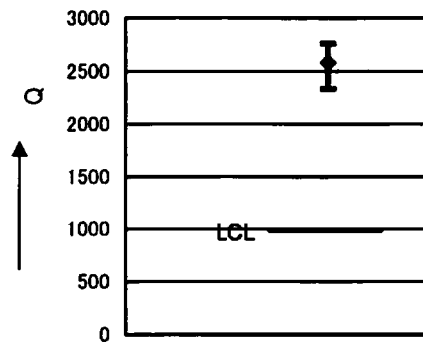
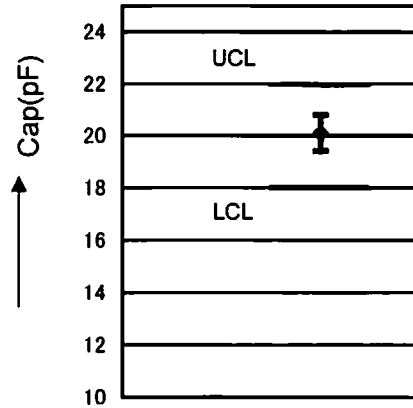
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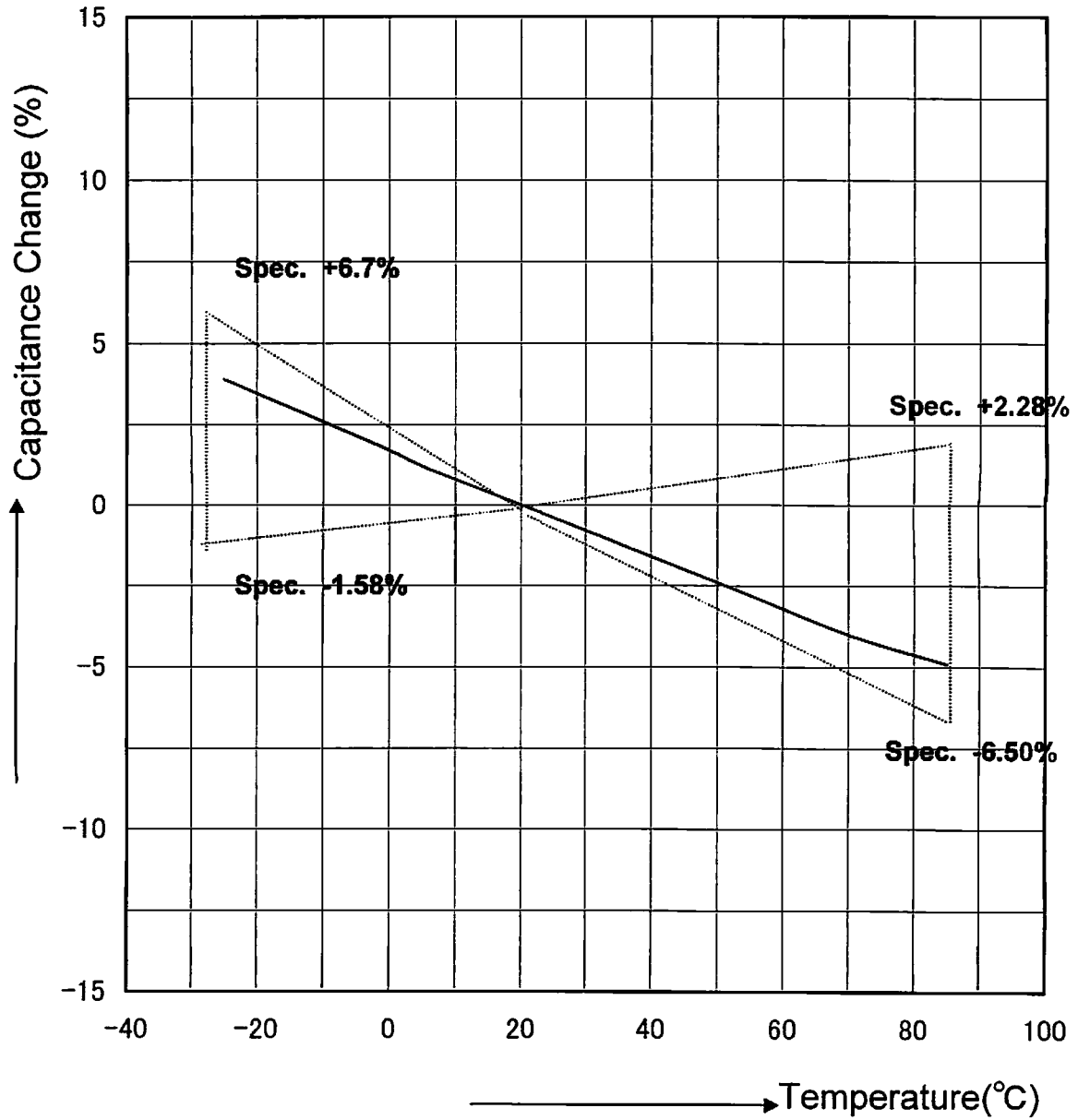
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試験項目 Test Item	1. 初期特性 Initial Characteristics	供試サンプル Specimen 試料数n=20 ECCD4D200KGE (SL/GP char. 20pF) <div style="float: right; border: 1px solid black; padding: 2px; width: 30px; text-align: center; margin-left: auto;">1</div>
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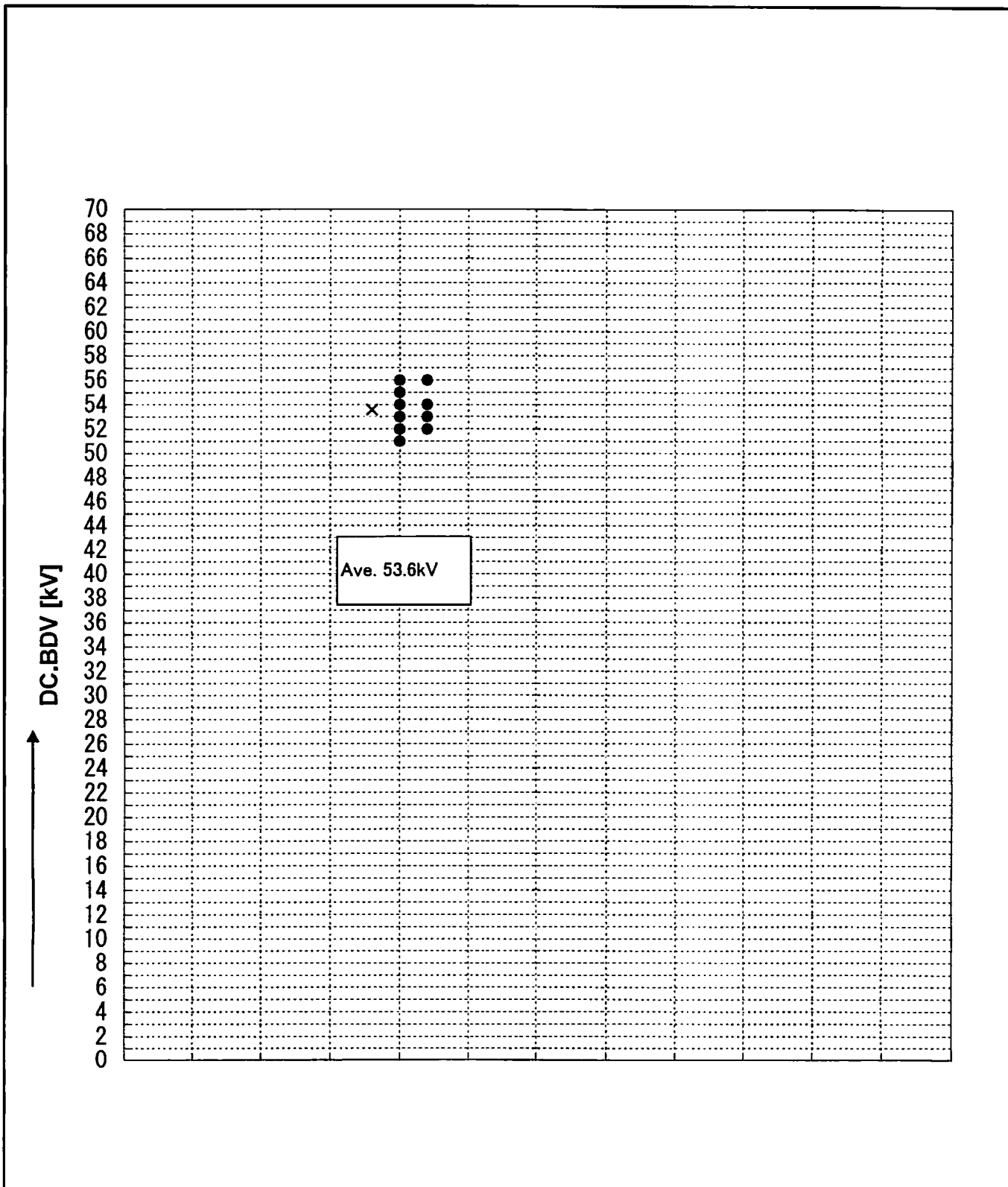
ECCD4D200KG



試験項目 Test Item	2.温度特性(特性SL 代表例) Temperature Characteristics Char.SL/GP /Typical	供試サンプル Specimen 試料数n=2 ECCD4D200KGE (SL/GP char. 20pF) <div style="float: right; border: 1px solid black; padding: 2px; margin-top: 5px;">2</div>
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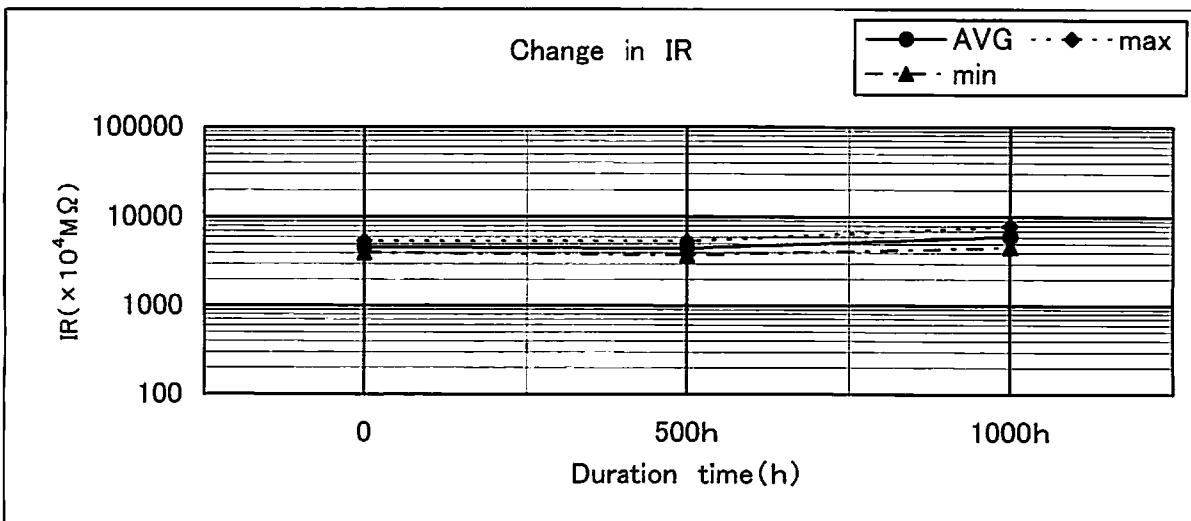
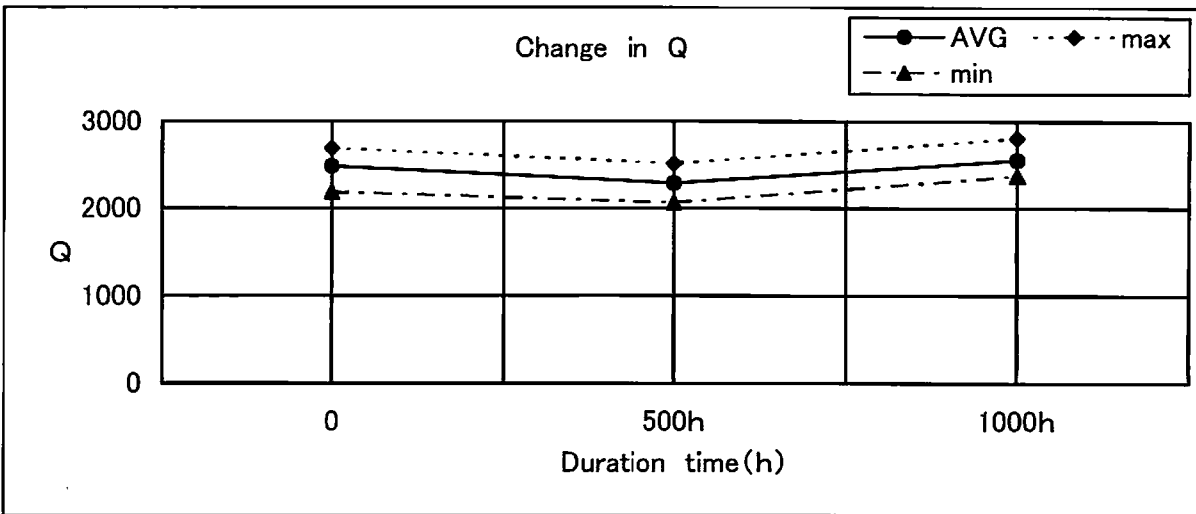
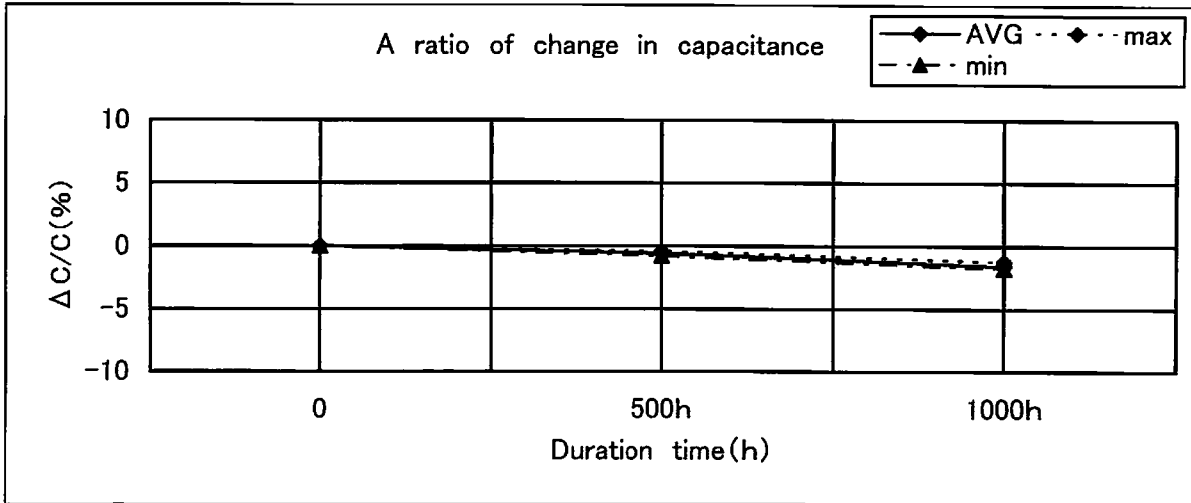
試験項目 Test Item	3. 昇圧破壊電圧(DC) Break Down Voltage (DC)	供試サンプル Specimen 試料数n=10 ECCD4D200KGE (SL char. 20pF)	<div style="border: 1px solid black; width: 30px; height: 30px; display: flex; align-items: center; justify-content: center; margin: 0 auto;"> 3 </div>
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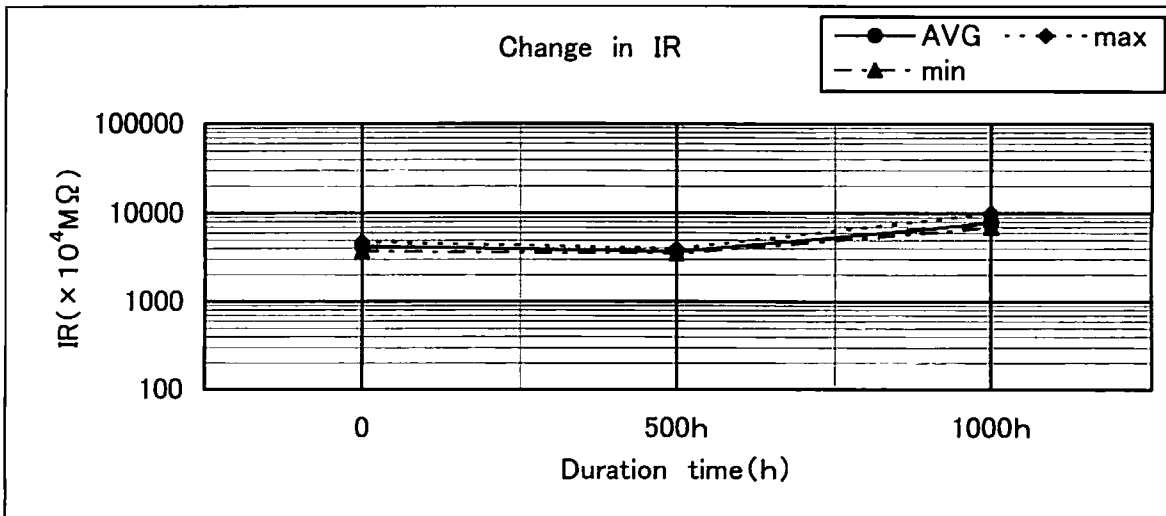
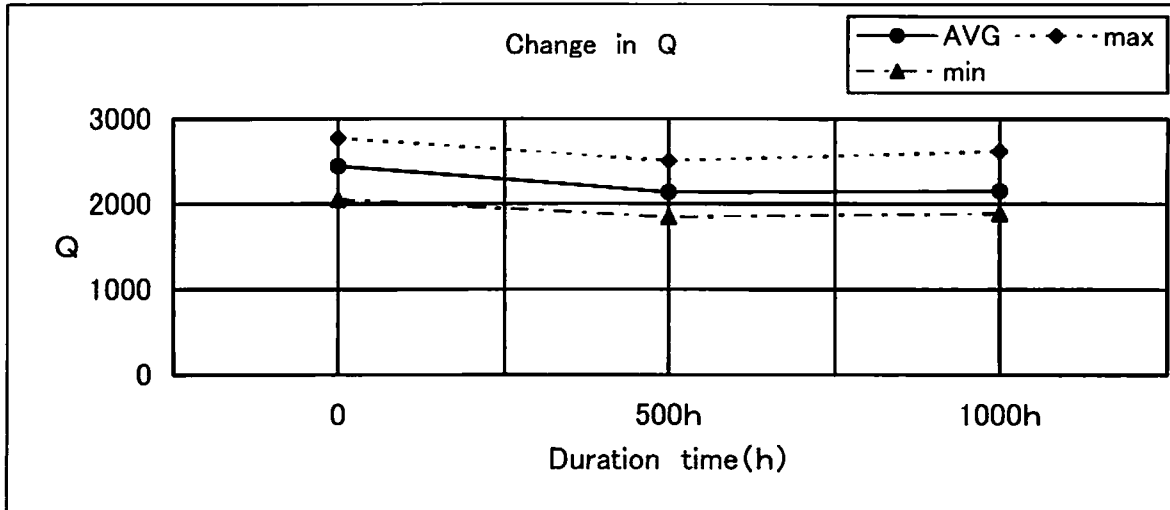
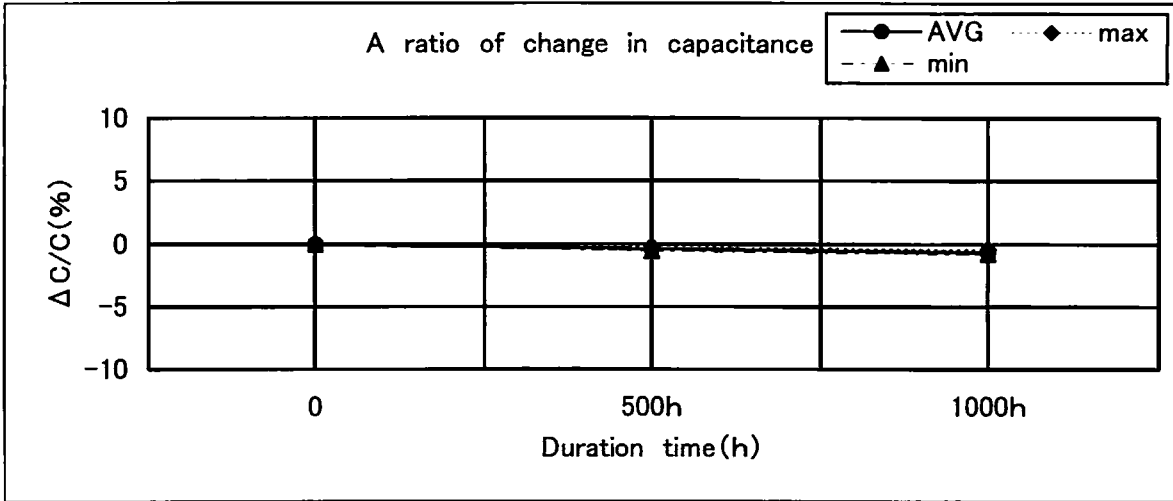
High Temperature steady state

4

Test Item A ratio of change in capacitance (1Vrms at 1MHz)
 Change in Q (1Vrms at 1MHz)
 Change in IR (DC500V at 30sec)
 Ambient temperature (25.0°C)
 Samples 20KV, 20pF, temp Char. SL
 Matsushita: ECCD4D200KGE
 Pieces (n=20)
 Test condition : Test Temperature 85°C



Test Item A ratio of change in capacitance (1Vrms at 1MHz)
 Change in Q (1Vrms at 1MHz)
 Change in IR (DC500V at 30sec)
 Ambient temperature (25.0°C)
Samples 20KV, 20pF, temp Char. SL
 Matsushita: ECCD4D200KGE
 Pieces (n=20)
Test condition : Test Temperature (85.0°C)
 DC 25.0 kV



Dump Heat steady state

6

Test Item A ratio of change in capacitance (1Vrms at 1MHz)
 Change in Q (1Vrms at 1MHz)
 Change in IR (DC500V at 30sec)
 Ambient temperature (25.0°C)
 Samples 20KV, 20pF, temp Char. SL
 Matsushita: ECCD4D200KGE
 Pieces (n=20)
 Test condition : Test Temperature & Humidity (60°C-95%)

